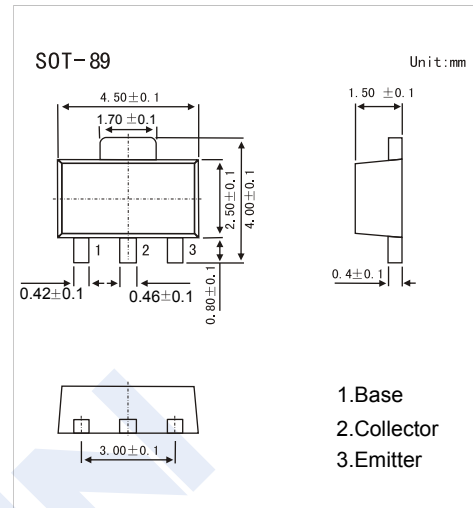


NPN Transistors

BCX54,BCX55,BCX56 (KCX54 ,KCX55,KCX56)

■ Features

- High current (max. 1 A).
- Low voltage (max. 80 V).



■ Absolute Maximum Ratings Ta = 25°C

Parameter		Symbol	Rating	Unit
Collector-base voltage	BCX54	V _{CBO}	45	V
	BCX55		60	V
	BCX56		100	V
Collector-emitter voltage	BCX54	V _{CEO}	45	V
	BCX55		60	V
	BCX56		80	V
Emitter-base voltage		V _{EBO}	5	V
Collector current		I _C	1	A
Peak collector current		I _{CM}	1.5	A
Peak base current		I _{BM}	0.2	A
Total power dissipation		P _{tot}	1.3	W
Storage temperature		T _{stg}	-65 to +150	°C
Junction temperature		T _j	150	°C
Operating ambient temperature		T _{amb}	-65 to +150	°C
Thermal resistance from junction to ambient		R _{th(j-a)}	94	K/W
Thermal resistance from junction to solder point		R _{th(j-s)}	14	K/W

BCX54,BCX55,BCX56■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current	I _{CBO}	V _{CB} = 30 V, I _E = 0			100	nA
		V _{CB} = 30 V, I _E = 0; T _j = 125°C			10	μA
Emitter cutoff current	I _{EBO}	V _{EB} = 5 V, I _C = 0			100	nA
DC current gain	h _{FE}	I _C = 5 mA; V _{CE} = 2 V	63			
		I _C = 150 mA; V _{CE} = 2 V	63		250	
		I _C = 500 mA; V _{CE} = 2 V	40			
DC current gain BCX54-10,BCX55-10,BCX56-10 BCX54-16,BCX55-16,BCX56-16	h _{FE}	I _C = 150 mA; V _{CE} = 2 V	63		160	
		I _C = 150 mA; V _{CE} = 2 V	100		250	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 500 mA; I _B = 50 mA			0.5	V
Base to emitter voltage	V _{BE}	I _C = 500 mA; V _{CE} = 2 V			1	V
Transition frequency	f _T	I _C = 10 mA; V _{CE} = 5 V; f = 100 MHz		130		MHz
DC current gain ratio of the complementary pairs	$\frac{h_{FE}}{h_{FE}}$	I _C = 150 mA; V _{CE} = 2 V		1.3	1.6	

■ h_{FE} Classification

TYPE	BCX54	BCX54-10	BCX54-16
Marking	BA	BC	BD

TYPE	BCX55	BCX55-10	BCX55-16
Marking	BE	BG	BM

TYPE	BCX56	BCX56-10	BCX56-16
Marking	BH	BK	BL

■ Typical Characteristics

